

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claim 1. (currently amended) A semiconductor light emitting device comprising:

a base body;

a selection mask formed on the base body, the selection mask defining a stripe-shaped opening having long-sides;

a wurtzite type compound semiconductor layer formed by selective growth from the opening such as to have a ridge line substantially parallel to the long-sides of the opening formed at the intersection of two crystal planes comprising one of a (1-101) plane and a (11-22) plane; and

a first conductive type cladding layer, an active layer, and a second conductive type cladding layer formed on the semiconductor layer

wherein the second conductive type cladding layer is formed said planes located on each side of the ridge line, wherein an electrode is formed in a region of the second conductive type cladding layer excluding a portion near the ridge line.

Claim 2. (previously presented) A semiconductor light emitting device according to claim 1, wherein an electrode is formed on only a region of the second conductive type cladding layer.

Claim 3. (cancelled)

Claim 4. (currently amended) A semiconductor light emitting device comprising: ~~according to claim 1~~

a base body;

a selection mask formed on the base body, the selection mask defining a stripe-shaped opening having long-sides;

a wurtzite type compound semiconductor layer formed by selective growth from the opening such as to have a ridge line substantially parallel to the long-sides of the opening formed

at the intersection of two crystal planes comprising one of a (1-101) plane and a (11-22) plane;
and

a first conductive type cladding layer, an active layer, and a second conductive type cladding layer formed on the semiconductor layer

wherein the second conductive type cladding layer is formed said planes located on each side of the ridge line, and

wherein an electrode is formed ~~only~~ in a region of the second conductive type cladding layer that is located on the pair of crystal planes and which has regular crystal steps.

Claim 5. (Cancelled)

Claim 6. (previously presented) A semiconductor light emitting device according to claim 1, wherein the wurtzite type compound semiconductor layer is a GaN based compound semiconductor layer.

Claim 7. (original) A semiconductor light emitting device according to claim 1, wherein the semiconductor light emitting device is one of a semiconductor laser and a light emitting diode.

Claim 8. (currently amended) A semiconductor light emitting device, comprising:

a base body;

a selection mask formed on the base body, the selection mask defining a stripe-shaped opening extending with a longitudinal direction taken as one of a (1-100) direction and a (11-20) direction;

a semiconductor layer formed by selective growth from the opening such as to have a ridge line substantially parallel to the longitudinal direction of the opening; and

a first conductive type cladding layer, an active layer, and a second conductive type cladding layer, which are formed on the semiconductor layer on a pair of crystal planes comprising one of a (1-101) and a (11-22) plane intersecting at said ridge line,

wherein an electrode is formed in a region of the second conductive type cladding layer excluding a portion near the ridge line.

Claim 9. (currently amended) A semiconductor light emitting device comprising:

a base body;

a selection mask formed on the base body the selection mask defining a stripe-shaped opening extending with a longitudinal direction taken as a direction tilted from one of a (1-100) direction and a (11-20) direction by an angle ranging from about 0.2° to about 20° ;

a semiconductor layer formed by selective growth from the opening such as to have a ridge line substantially parallel to the longitudinal direction of the opening; and

a first conductive type cladding layer, an active layer, and a second conductive type cladding layer, which are formed on the semiconductor layer on a pair of crystal planes comprising one of a (1-101) and a (11-22) plane intersecting at said ridge line,

wherein an electrode is formed in a region of the second conductive type cladding layer excluding a portion near the ridge line.

Claim 10. (currently amended) A display unit including an array of a plurality of semiconductor light emitting devices, each device comprising:

a base body;

a selection mask formed in the base body the selection mask defining a stripe-shaped opening having long-sides;

a semiconductor layer formed by selective growth from the opening such as to have a ridge line substantially parallel to the long-sides of the opening; and

a first conductive type cladding layer, an active layer, and a second conductive type cladding layer, which are formed on the semiconductor layer on a pair of crystal planes comprising one of a (1-101) and a (11-22) plane intersecting at said ridge line,

wherein an electrode is formed in a region of the second conductive type cladding layer excluding a portion near the ridge line.

Claims 11 – 13. (Cancelled)